imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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PHOTONIC Silicon Photodiode, Blue Enhanced Photoconductive **DETECTORS INC.** (MRD 510) Industry Equivalent Type PDB-C120



PACKAGE DIMENSIONS INCH [mm] 45 0.50 [12.7] MIN 0.040 0.145 [3.68] 0.145 [3.68] Ø0.019 [0.48] Ø0.016 [0.41] WIRE BOND Ø0.195 [4.95] Ø0.178 [4.52] 0.100 [2.54] ANODE CATHODE & CASE PHOTODIODE CHIP WINDOW CAP Ø0.209 5.31 0.025 [0.64] (WELDED) 0.027 [0.69] 0.022 0.56 HEADER SOUARE Ø0.012 [Ø0.30] TO-46 HERMETIC CAN PACKAGE ACTIVE AREA ACTIVE AREA = 0.073 mm^2

FEATURES

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

DESCRIPTION

The **PDB-C120** is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-46 metal can with a flat window.

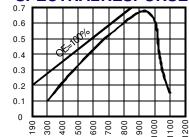
APPLICATIONS

- Fiber optic
- Laser detection
- Light demodulation
- Matched to I.R. LEDs

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		200	V
T _{STG}	Storage Temperature	-65	+150	S
T _o	Operating Temperature Range	-55	+125	с
T _s	Soldering Temperature*		+240	с
Ι	Light Current		500	mA

SPECTRALRESPONSE



WAVELENGTH(nm)

RESPONSIVITY (A/W)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
ا _{عد}	Short Circuit Current	H = 100 fc, 2850 K	1.2	1.5		μA			
I _D	Dark Current	$H = 0, V_{R} = 10 V$		0.5	2.0	nA			
R _{SH}	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	400	500		MΩ			
TC R _{SH}	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		% / °C			
CJ	Junction Capacitance	$H = 0, V_{R} = 10 V^{**}$		1		рF			
λrange	Spectral Application Range	Spot Scan	350		1100	nm			
λρ	Spectral Response - Peak	Spot Scan		950		nm			
V _{BR}	Breakdown Voltage	I = 10 µµ A	100	150		V			
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		9.0x10 ⁻¹⁵		W/\sqrt{Hz}			
tr	Response Time	$RL = 1 K\Omega V_R = 50 V$		1.0		nS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f=1 MHz [FORM NO. 100-PDB-C120 REV B]